

FEATURES

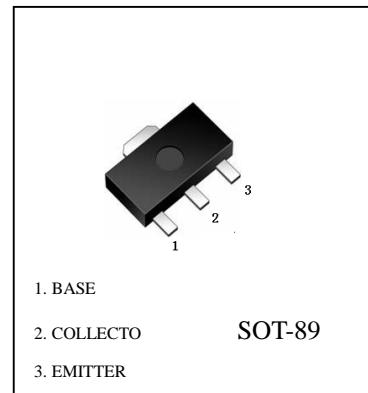
- Small size making it easy to provide high-density,small-sized hybrid IC's.

Marking: CH

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current -Continuous	I _C	1	A
Collector Power dissipation	P _C	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

2SC4272 (NPN)



ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =10uA,I _E =0	75			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA,I _B =0	45			V
Emitter-base breakdown voltage	V _{EBO}	I _E =10uA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =5V,I _C =500mA	60		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =0.5A, I _B =0.05A		0.2	0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =0.5A, I _B =0.05A		0.9	1.2	V
Transition frequency	f _T	V _{CE} =10V,I _C =50mA	180	250		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0,f=1MHz		15		pF

2SC4272 Typical Characteristics
